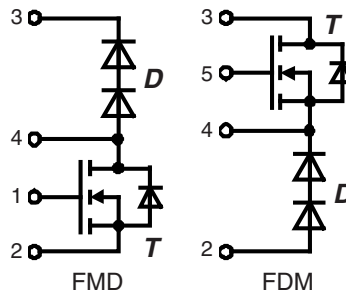


# CoolMOS™<sup>1)</sup> Power MOSFET with HiPerDyn™ FRED

## Buck and Boost Topologies

Electrically isolated back surface  
2500 V electrical isolation  
N-Channel Enhancement Mode  
Low  $R_{DS(on)}$ , high  $V_{DSS}$  MOSFET  
Ultra low gate charge

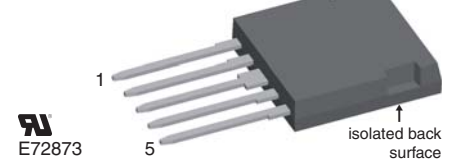


$$I_{D25} = 47 \text{ A}$$

$$V_{DSS} = 600 \text{ V}$$

$$R_{DS(on) \text{ max}} = 0.045 \text{ } \Omega$$

### ISOPLUS i4™



MOSFET T			
Symbol	Conditions	Maximum Ratings	
$V_{DSS}$	$T_{VJ} = 25^\circ\text{C}$	600	V
$V_{GS}$		$\pm 20$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	47	A
$I_{D90}$	$T_C = 90^\circ\text{C}$	32	A
$E_{AS}$ $E_{AR}$	single pulse repetitive } $I_D = 11 \text{ A}; T_C = 25^\circ\text{C}$	1950 3	mJ mJ
$dV/dt$	MOSFET $dV/dt$ ruggedness $V_{DS} = 0 \dots 480 \text{ V}$	50	V/ns

### Features

- Silicon chip on Direct-Copper-Bond substrate
  - high power dissipation
  - isolated mounting surface
  - 2500 V electrical isolation
  - low drain to tab capacitance ( $< 40 \text{ pF}$ )
- Fast CoolMOS™<sup>1)</sup> power MOSFET 4<sup>th</sup> generation
  - high blocking capability
  - lowest resistance
  - avalanche rated for unclamped inductive switching (UIS)
  - low thermal resistance due to reduced chip thickness
- Enhanced total power density
- HiPerDyn™ FRED
  - consisting of series connected diodes
  - enhanced dynamic behaviour for high frequency operation

Symbol	Conditions	Characteristic Values				
		$(T_{VJ} = 25^\circ\text{C}, \text{ unless otherwise specified})$				
		min.	typ.	max.		
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}; I_D = 44 \text{ A}$		40	45	m $\Omega$	
$V_{GS(th)}$	$V_{DS} = V_{GS}; I_D = 3 \text{ mA}$	2.5	3	3.5	V	
$I_{DSS}$	$V_{DS} = V_{DSS}; V_{GS} = 0 \text{ V}$			10	$\mu\text{A}$	
				50	$\mu\text{A}$	
$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			100	nA	
$C_{iss}$ $C_{oss}$	} $V_{GS} = 0 \text{ V}; V_{DS} = 100 \text{ V}$ $f = 1 \text{ MHz}$		6800		pF	
				320		pF
$Q_g$ $Q_{gs}$ $Q_{gd}$	} $V_{GS} = 0 \text{ to } 10 \text{ V}; V_{DS} = 400 \text{ V}; I_D = 44 \text{ A}$		150	190	nC	
				35		nC
				50		nC
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $E_{on}$ $E_{off}$ $E_{rec off}$	} $V_{GS} = 10 \text{ V}; V_{DS} = 400 \text{ V}$ $I_D = 44 \text{ A}; R_G = 3.3 \text{ } \Omega$		30		ns	
				20		ns
				100		ns
				10		ns
				tbd		mJ
				tbd		mJ
				tbd		mJ
$R_{thJC}$ $R_{thCH}$	with heat transfer paste		0.25	0.45	K/W K/W	

### Applications

- Switched mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Power factor correction (PFC)

### Advantages

- Easy assembly: no screws or isolation foils required
- Space savings
- High power density
- High reliability

<sup>1)</sup> CoolMOS™ is a trademark of Infineon Technologies AG.

**MOSFET T Source-Drain Diode**

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
( $T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified)					
$I_S$	$V_{GS} = 0\text{ V}$			44	A
$V_{SD}$	$I_F = 44\text{ A}; V_{GS} = 0\text{ V}$		0.9	1.2	V
$t_{rr}$	$I_F = 44\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}; V_R = 400\text{ V}$		600		ns
$Q_{RM}$			17		$\mu\text{C}$
$I_{RM}$			60		A

**Diode D (data for series connection)**

Symbol	Conditions	Maximum Ratings	
$V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600	V
$I_{F25}$	$T_C = 25^{\circ}\text{C}$	95	A
$I_{F90}$	$T_C = 90^{\circ}\text{C}$	56	A

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
$V_F$	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$		2.48	V
				3.02	V
	$I_F = 60\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$		1.89	A
				2.45	A
$I_R$	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$		1	$\mu\text{A}$
		$T_{VJ} = 150^{\circ}\text{C}$		0.2	mA
$I_{FSM}$	$t = 10\text{ ms (50 Hz), sine};$	$T_{VJ} = 45^{\circ}\text{C}$		450	A
$I_{RM}$	$I_F = 30\text{ A}; V_R = 100\text{ V};$ $-di_F/dt = 200\text{ A}/\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$		2	A
$t_{rr}$				30	ns
$R_{thJC}$	with heat transfer paste		0.25	0.55	K/W
$R_{thCH}$					K/W

**Component**

Symbol	Conditions	Maximum Ratings	
$T_{VJ}$	operating	-55...+150	$^{\circ}\text{C}$
$T_{stg}$	storage	-55...+125	$^{\circ}\text{C}$
$V_{ISOL}$	$I_{ISOL} < 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
$F_C$	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
$C_P$	coupling capacity between shorted pins and mounting tab in the case		40		pF
$d_S, d_A$	pin - pin	1.7			mm
$d_S, d_A$	pin - backside metal	5.5			mm
Weight			9		g

ISOPLUS i4™ Outline

